

Data Sheet January 2000 File Number 3211.3

50A, 600V Ultrafast Diode

The RURG5060 is an ultrafast diode with soft recovery characteristics (t_{rr} < 65ns). It has low forward voltage drop and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristic minimizes ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

Formerly developmental type TA09909.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURG5060	TO-247	RURG5060

NOTE: When ordering, use the entire part number.

Symbol



Features

Ultrafast with Soft Recovery	<65ns
Operating Temperature	175°C
Reverse Voltage	600V
Avalanche Energy Rated	

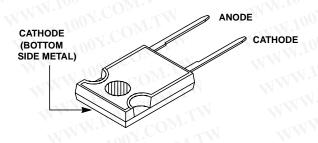
Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE 2 LEAD TO-247



Absolute Maximum Ratings T_C = 25°C, Unless Otherwise Specified

	RURG5060	UNITS
Peak Repetitive Reverse VoltageV _{RRM}	600	V
Working Peak Reverse Voltage	600	V
DC Blocking VoltageV _R	600	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_C = 102^{\circ}C$)	50	A
Repetitive Peak Surge Current	100	MITIA
Nonrepetitive Peak Surge Current	500	Α
Maximum Power Dissipation	150	W
Avalanche Energy (See Figures 7 and 8)	40	mJ
Operating and Storage Temperature	-65 to 175	oC

勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V _F	I _F = 50A	OMITW	M	1.6	V
	I _F = 50A, T _C = 150 ^o C	OMITH	- 11	1.4	OM·V
I _R	V _R = 600V	CONTIN	-	250	μΑ
	$V_R = 600V, T_C = 150^{\circ}C$	COMITY	- 1	1.5	mA
NW. CO	I _F = 1A, dI _F /dt = 100A/μs	COM.T		65	ns
	$I_F = 50A$, $dI_F/dt = 100A/\mu s$	OM.	_	75	ns
t _a	I _F = 50A, dI _F /dt = 100A/μs	OOY	30	WW.1	ns
t _b	I _F = 50A, dI _F /dt = 100A/μs	1001.	20	- WW	ns
$R_{ hetaJC}$	TILL 100 Y. COMITW	N.100 J.	William	1	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 t_{rr} = Reverse recovery time at dI_F/dt = 100A/ μ s (See Figure 6), summation of t_a + t_b

 t_a = Time to reach peak reverse current at dI_F/dt = 100A/ μ s (See Figure 6).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

 $R_{\theta JC}$ = Thermal resistance junction to case

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

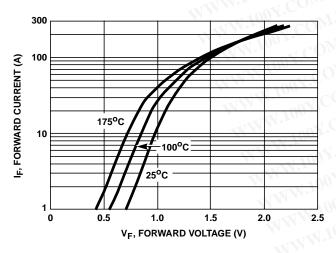


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

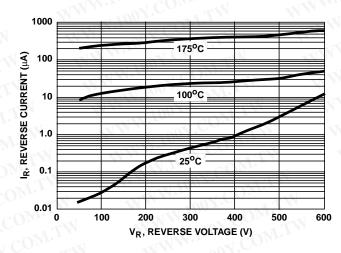


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

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Typical Performance Curves (Continued)

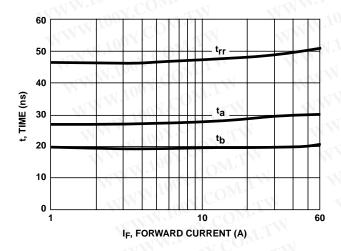


FIGURE 3. t_{rr}, t_a AND t_b CURVES vs FORWARD CURRENT

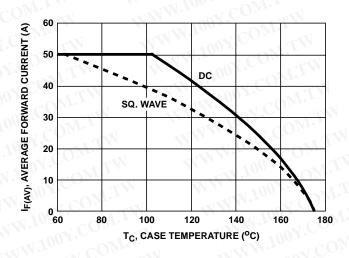


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

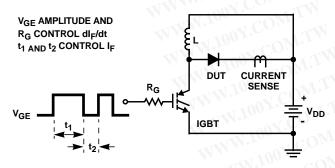


FIGURE 5. t_{rr} TEST CIRCUIT

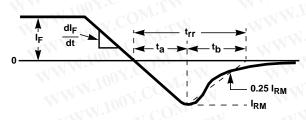


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

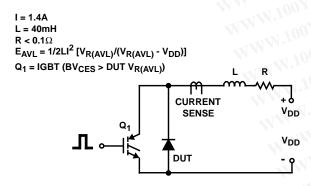


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

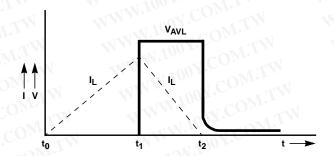


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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